

ASYMMETRIC-AREA MEMORY CELL

ABSTRACT OF THE INVENTION

An asymmetric-area memory cell, and a fabrication method
5 for forming an asymmetric-area memory cell, are provided. The method
comprises: forming a bottom electrode having an area; forming a CMR
memory film overlying the bottom electrode, having an asymmetric area;
and, forming a top electrode having an area, less than the bottom
electrode area, overlying the CMR film. In one aspect, the CMR film has a
10 first area adjacent the top electrode and a second area, greater than the
first area, adjacent the bottom electrode. Typically, the CMR film first
area is approximately equal to the top electrode area, although the CMR
film second area may be less than the bottom electrode area.